International
IOR Rectifier

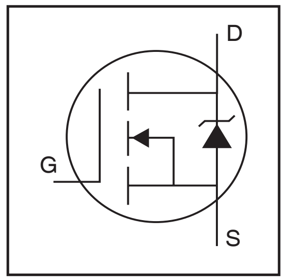
PD - 97078A

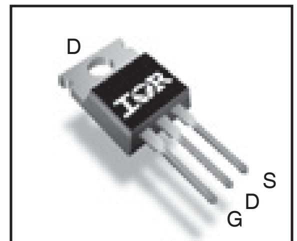
IRFB4229PbF

Features

- Advanced Process Technology
- Key Parameters Optimized for PDP Sustain, Energy Recovery and Pass Switch Applications
- Low E_{PULSE} Rating to Reduce Power Dissipation in PDP Sustain, Energy Recovery and Pass Switch Applications
- Low Q_G for Fast Response
- High Repetitive Peak Current Capability for Reliable Operation
- Short Fall & Rise Times for Fast Switching
- 175°C Operating Junction Temperature for Improved Ruggedness
- Repetitive Avalanche Capability for Robustness and Reliability
- Class-D Audio Amplifier 300W-500W (Half-bridge)

Key Parameters		
V_{DS} min	250	V
$V_{DS\ (Avalanche)}$ typ.	300	V
$R_{DS(ON)}$ typ. @ 10V	38	mΩ
I_{RP} max @ T_C= 100°C	91	A
T_J max	175	°C





TO-220AB

G	D	S
Gate	Drain	Source

Description

This HEXFET® Power MOSFET is specifically designed for Sustain; Energy Recovery & Pass switch applications in Plasma Display Panels. This MOSFET utilizes the latest processing techniques to achieve low on-resistance per silicon area and low E_{PULSE} rating. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GS}	Gate-to-Source Voltage	±30	V
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	46	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	33	
I_{DM}	Pulsed Drain Current ①	180	
I_{RP} @ T_C = 100°C	Repetitive Peak Current ⑤	91	
P_D @T_C = 25°C	Power Dissipation	330	W
P_D @T_C = 100°C	Power Dissipation	190	
	Linear Derating Factor	2.2	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-40 to + 175	°C
	Soldering Temperature for 10 seconds	300	
	Mounting Torque, 6-32 or M3 Screw	10lb·in (1.1N·m)	N

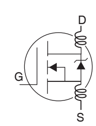
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	0.45	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ④	—	62	

Notes ① through ⑤ are on page 8

09/10/07

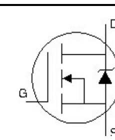
Electrical Characteristics @ $T_J = 25°C$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	250	–––	–––	V	$V_{GS} = 0V$, $I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	210	–––	mV/°C	Reference to 25°C, $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	38	46	mΩ	$V_{GS} = 10V$, $I_D = 26A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	–––	5.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	–––	-14	–––	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	20	μA	$V_{DS} = 250V$, $V_{GS} = 0V$
		–––	–––	1.0	mA	$V_{DS} = 250V$, $V_{GS} = 0V$, $T_J = 125°C$
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	–––	–––	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	83	–––	–––	S	$V_{DS} = 25V$, $I_D = 26A$
Q_g	Total Gate Charge	–––	72	110	nC	$V_{DD} = 125V$, $I_D = 26A$, $V_{GS} = 10V$③
Q_{gd}	Gate-to-Drain Charge	–––	26	–––		
$t_{d(on)}$	Turn-On Delay Time	–––	18	–––	ns	$V_{DD} = 125V$, $V_{GS} = 10V$ ③
t_r	Rise Time	–––	31	–––		$I_D = 26A$
$t_{d(off)}$	Turn-Off Delay Time	–––	30	–––		$R_G = 2.4\Omega$
t_f	Fall Time	–––	21	–––		See Fig. 22
t_{st}	Shoot Through Blocking Time	100	–––	–––	ns	$V_{DD} = 200V$, $V_{GS} = 15V$, $R_G = 4.7\Omega$
E_{PULSE}	Energy per Pulse	–––	790	–––	μJ	L = 220nH, C= 0.3μF, $V_{GS} = 15V$ $V_{DS} = 200V$, $R_G = 4.7\Omega$, $T_J = 25°C$
		–––	1390	–––		L = 220nH, C= 0.3μF, $V_{GS} = 15V$ $V_{DS} = 200V$, $R_G = 4.7\Omega$, $T_J = 100°C$
C_{iss}	Input Capacitance	–––	4560	–––	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	–––	390	–––		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	–––	100	–––		ƒ = 1.0MHz,
C_{oss} eff.	Effective Output Capacitance	–––	290	–––		$V_{GS} = 0V$, $V_{DS} = 0V$ to 200V
L_D	Internal Drain Inductance	–––	4.5	–––	nH	Between lead, 6mm (0.25in.)
L_S	Internal Source Inductance	–––	7.5	–––		from package and center of die contact 

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	–––	130	mJ
E_{AR}	Repetitive Avalanche Energy ①	–––	33	mJ
$V_{DS(Avalanche)}$	Repetitive Avalanche Voltage ①	300	–––	V
I_{AS}	Avalanche Current ②	–––	26	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S @ $T_C = 25°C$	Continuous Source Current (Body Diode)	–––	–––	46	A	MOSFET symbol showing the
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	180		integral reverse p-n junction diode. 
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	$T_J = 25°C$, $I_S = 26A$, $V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	–––	190	290	ns	$T_J = 25°C$, $I_F = 26A$, $V_{DD} = 50V$
Q_{rr}	Reverse Recovery Charge	–––	840	1260	nC	di/dt = 100A/μs ③

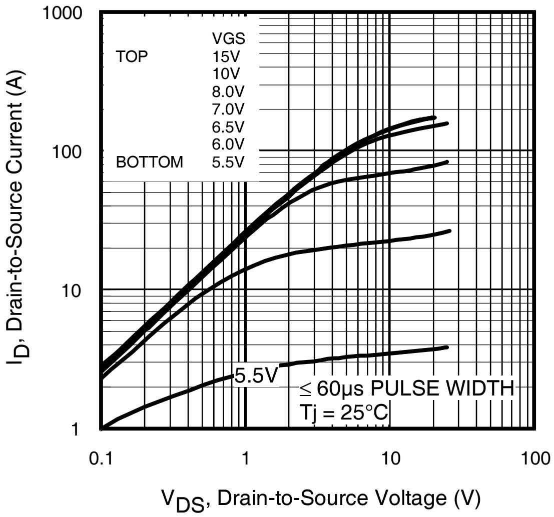


Fig 1. Typical Output Characteristics

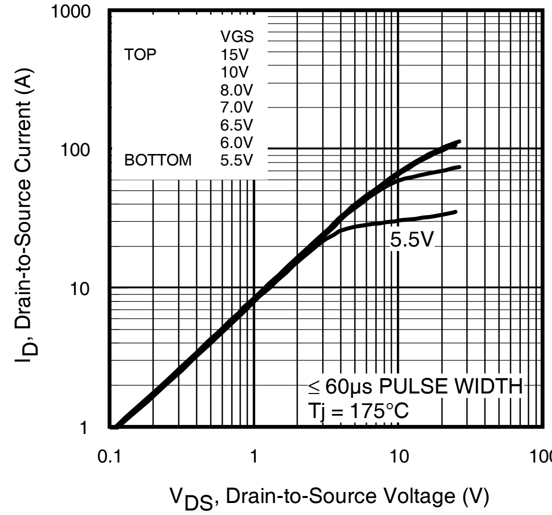


Fig 2. Typical Output Characteristics

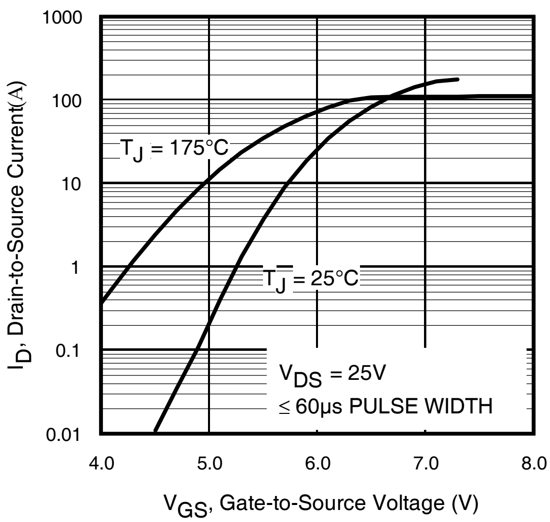


Fig 3. Typical Transfer Characteristics

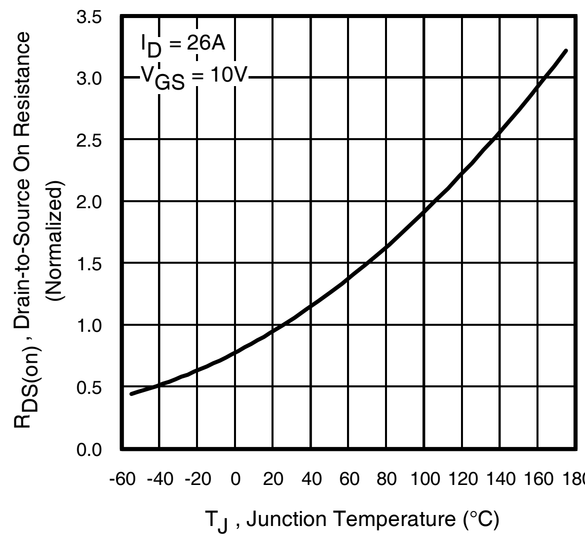


Fig 4. Normalized On-Resistance vs. Temperature

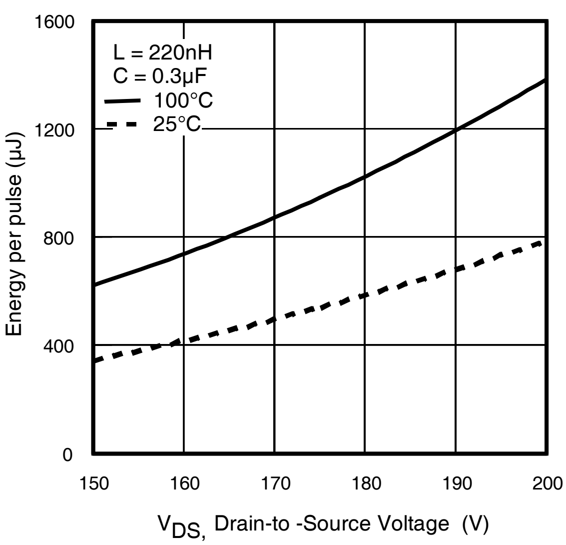


Fig 5. Typical E_{PULSE} vs. Drain-to-Source Voltage

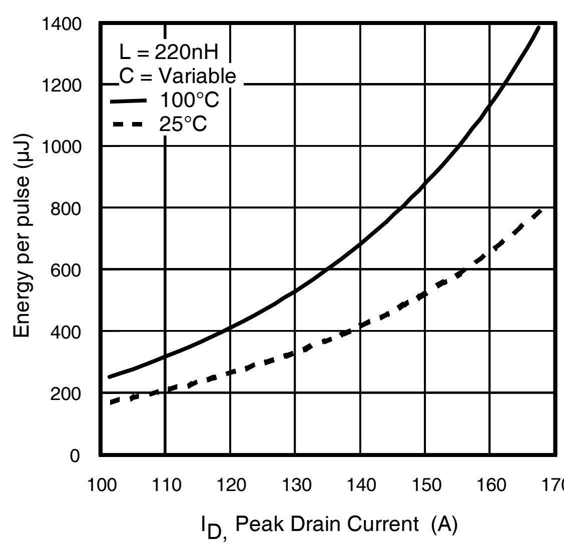


Fig 6. Typical E_{PULSE} vs. Drain Current

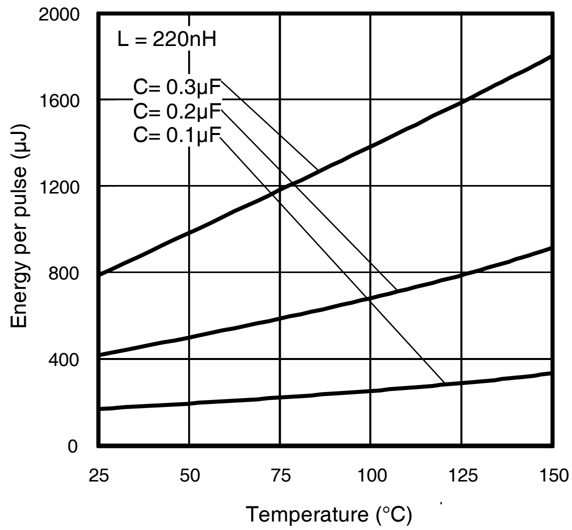


Fig 7. Typical E_{PULSE} vs.Temperature

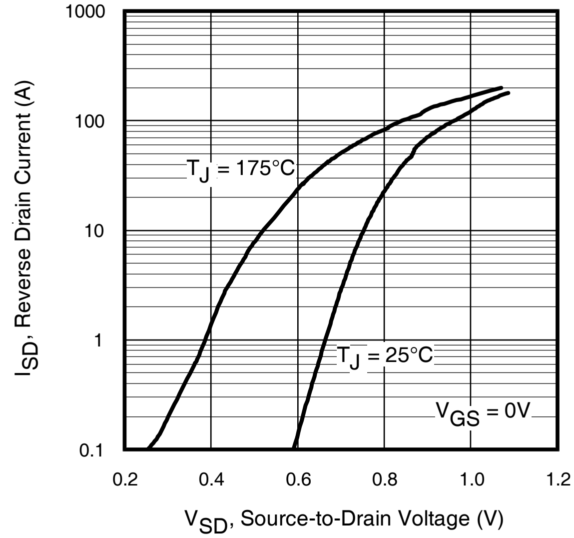


Fig 8. Typical Source-Drain Diode Forward Voltage

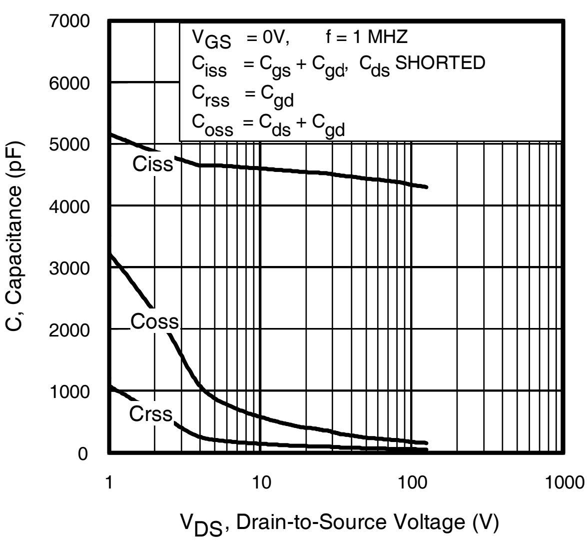


Fig 9. Typical Capacitance vs.Drain-to-Source Voltage

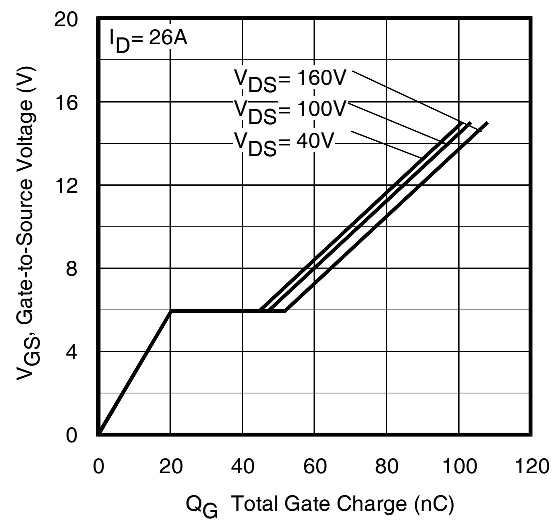


Fig 10. Typical Gate Charge vs.Gate-to-Source Voltage

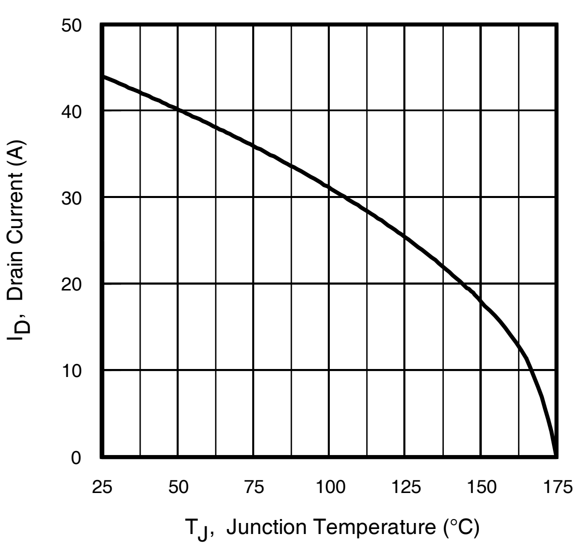


Fig 11. Maximum Drain Current vs. Case Temperature

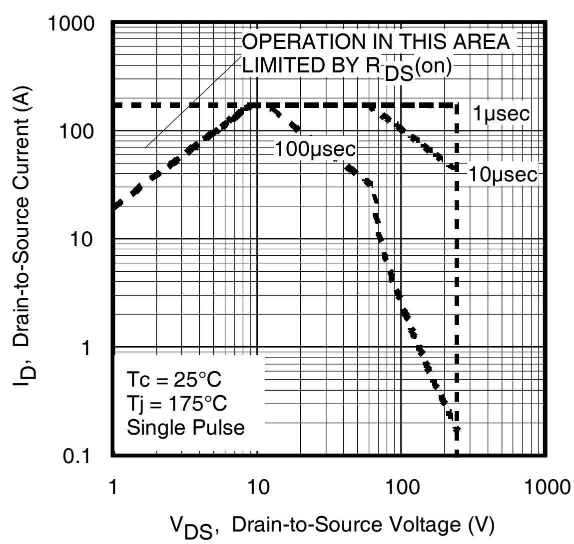


Fig 12. Maximum Safe Operating Area

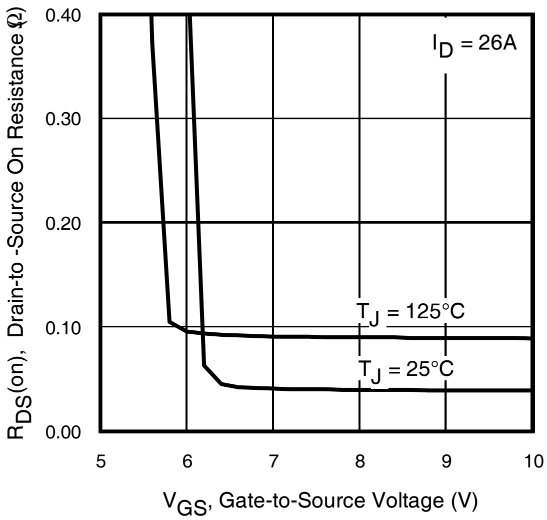


Fig 13. On-Resistance Vs. Gate Voltage

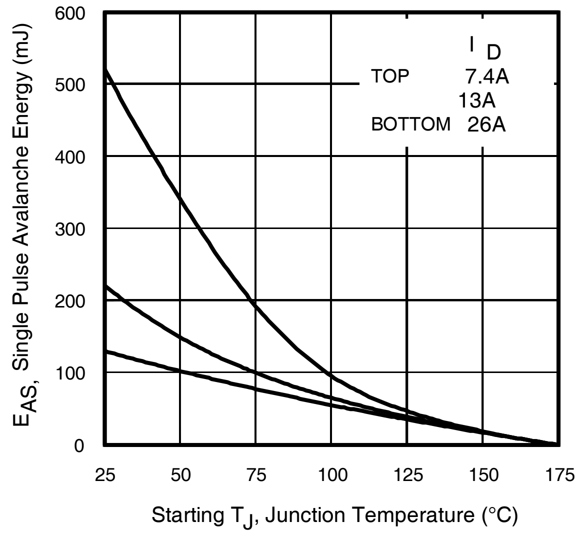


Fig 14. Maximum Avalanche Energy Vs. Temperature

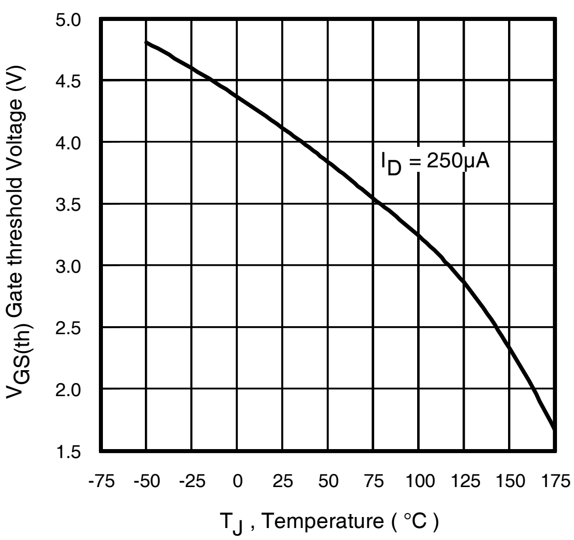


Fig 15. Threshold Voltage vs. Temperature

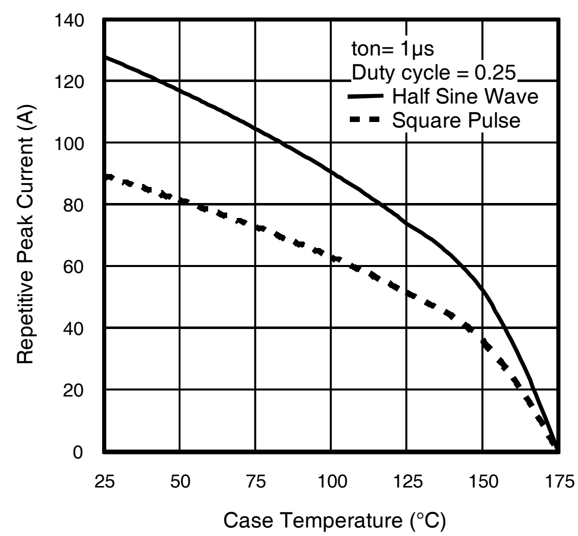
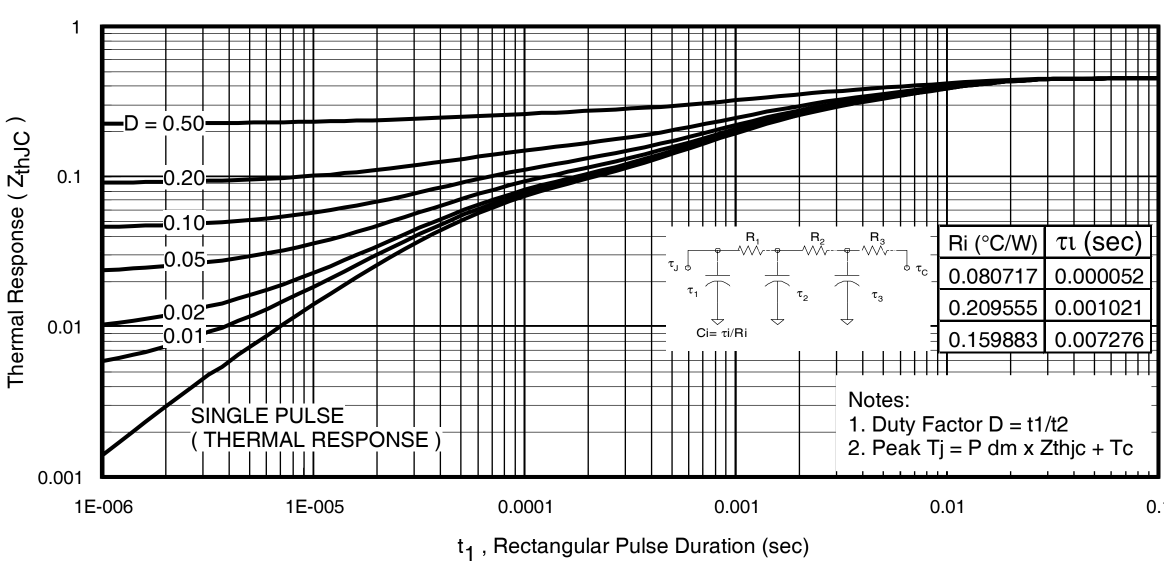
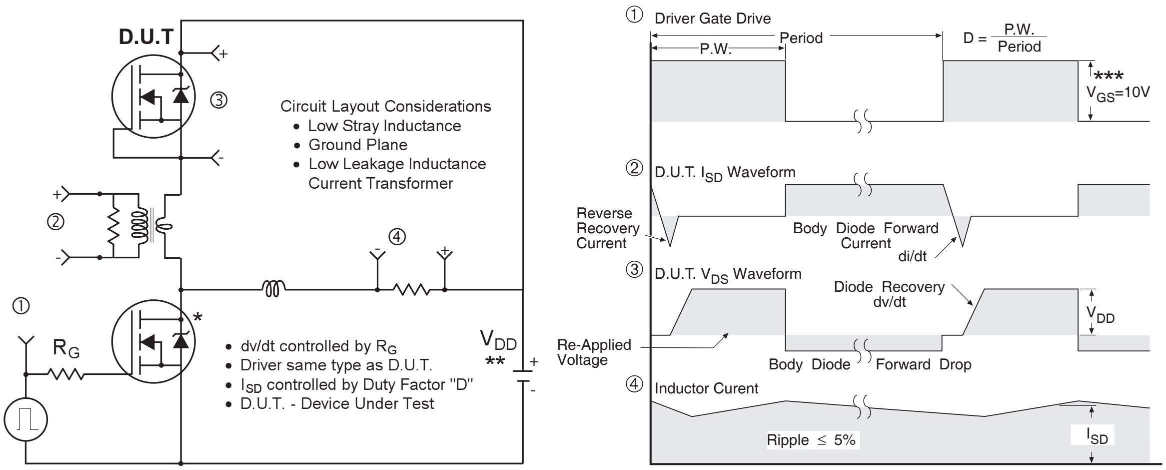


Fig 16. Typical Repetitive peak Current vs. Case temperature



Ri (°C/W)	τι (sec)
0.080717	0.000052
0.209555	0.001021
0.159883	0.007276

Fig 17. Maximum Effective Transient Thermal Impedance, Junction-to-Case



* Use P-Channel Driver for P-Channel Measurements

** Reverse Polarity for P-Channel

*** V_{GS} = 5V for Logic Level Devices

Fig 18. Diode Reverse Recovery Test Circuit for HEXFET® Power MOSFETs

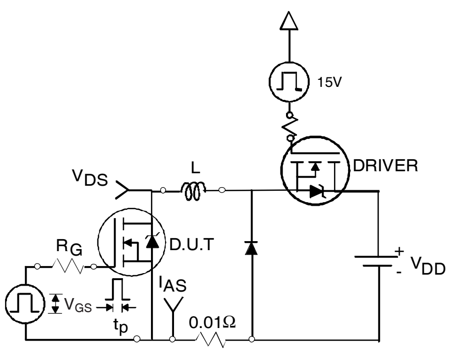


Fig 19a. Unclamped Inductive Test Circuit

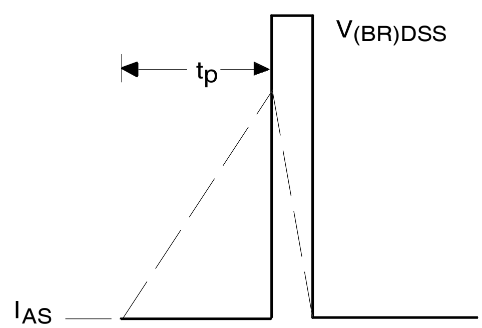


Fig 19b. Unclamped Inductive Waveforms

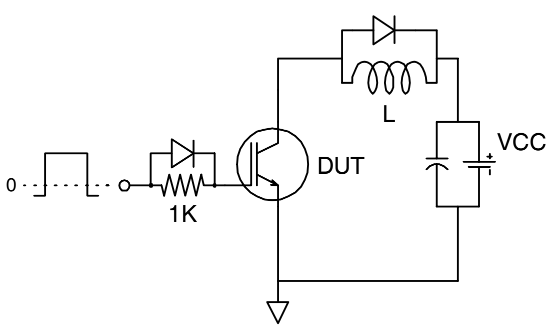


Fig 20a. Gate Charge Test Circuit

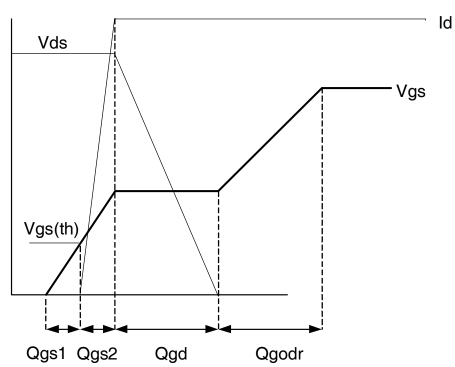


Fig 20b. Gate Charge Waveform

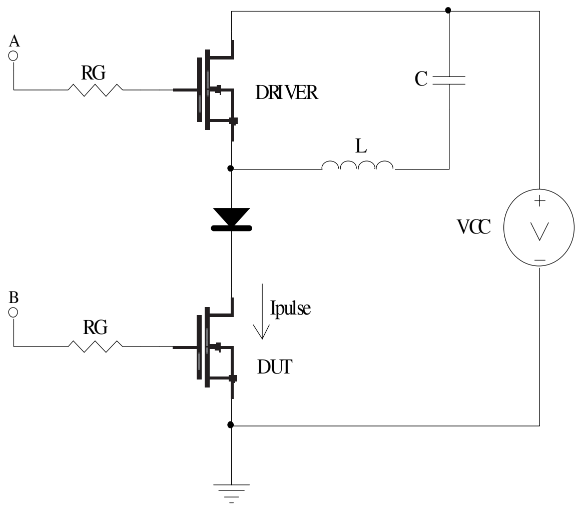


Fig 21a. t_{st} and E_{PULSE} Test Circuit

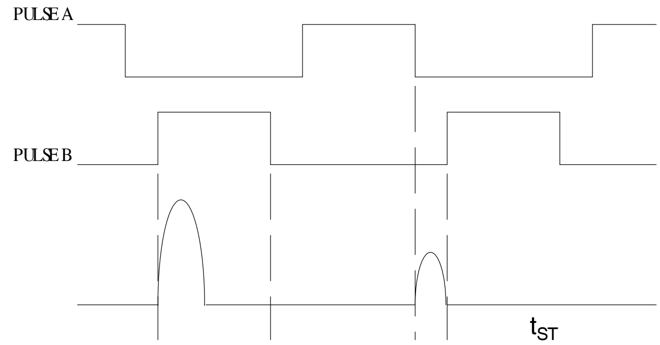


Fig 21b. t_{st} Test Waveforms

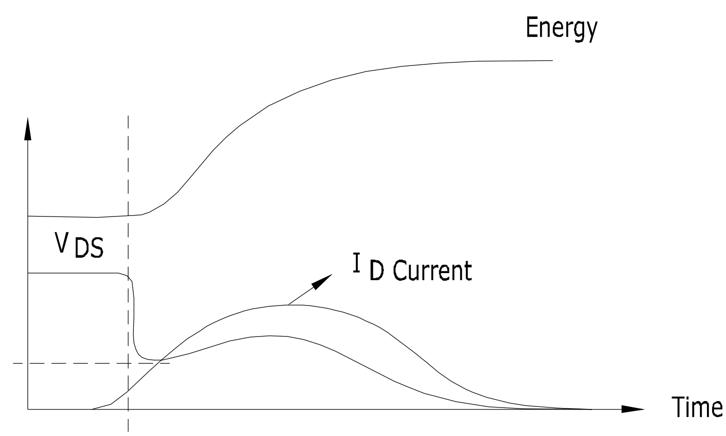


Fig 21c. E_{PULSE} Test Waveforms

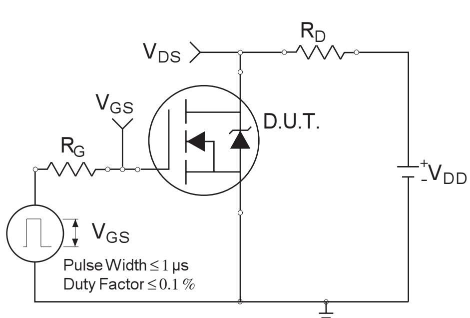


Fig 22a. Switching Time Test Circuit

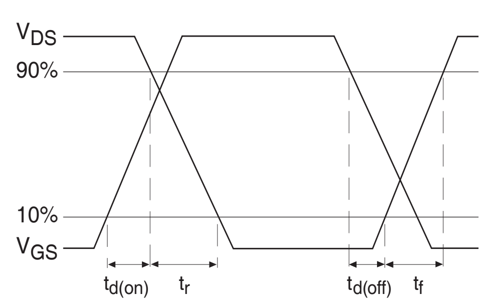
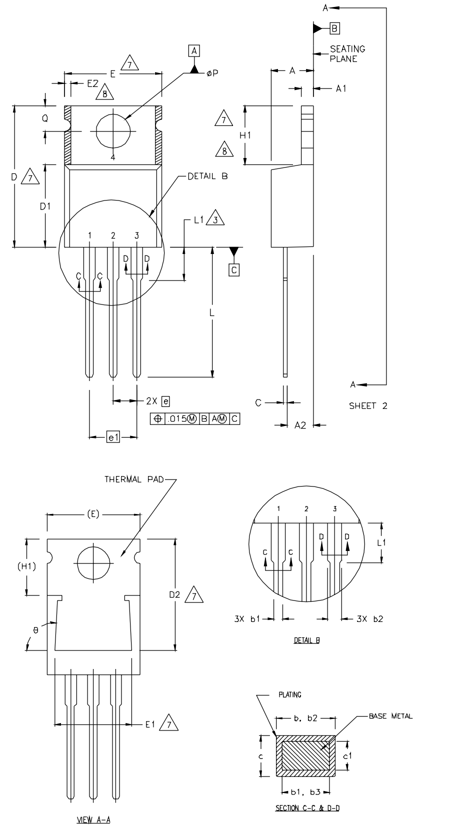


Fig 22b. Switching Time Waveforms

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3. LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION : INCHES.
7. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8. DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	–	6.35	–	.250	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
ø	90°–93°		90°–93°		

LEAD ASSIGNMENTS

HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE

IGBTs, CoPACK

1.- GATE
2.- COLLECTOR
3.- EMITTER

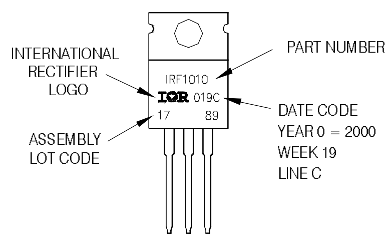
DIODES

1.- ANODE/OPEN
2.- CATHODE
3.- ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 2000
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.
② Starting T_J = 25°C, L = 0.37mH, R_G = 25Ω, I_{AS} = 26A.
③ Pulse width ≤ 400μs; duty cycle ≤ 2%.
④ R_θ is measured at T_J of approximately 90°C.
⑤ Half sine wave with duty cycle = 0.25, ton=1μsec.

Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information. 09/2007

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie") .

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (**www.infineon.com**).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFETs ***category:***

Click to view products by Infineon ***manufacturer:***

Other Similar products are found below :

MCH3443-TL-E MCH6422-TL-E NTNS3A92PZT5G IRFD120 2SK2464-TL-E 2SK3818-DL-E 2SJ277-DL-E 2SK2267(Q) MIC4420CM-TR IRFS350 IPS70R2K0CEAKMA1 AON6932A TS19452CS RL 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG NTE2384 2N7000TA DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 STU7N60DM2 DMTH10H4M6SPS-13 DMN2990UFB-7B 2N7002W-G MCQ7328-TP IPB45P03P4L11ATMA2 BXP4N65F BXP2N20L BXP2N65D TSM60NB380CP ROG SLF10N65ABV2 IRF9395MTRPBF FCMT080N65S3 NTD5C632NLT4G NTMFS0D55N03CGT1G NTMFS1D15N03CGT1G NTMTS0D4N04CTXG NTMTS1D6N10MCTXG NTMYS2D1N04CLTWG NVD360N65S3T4G